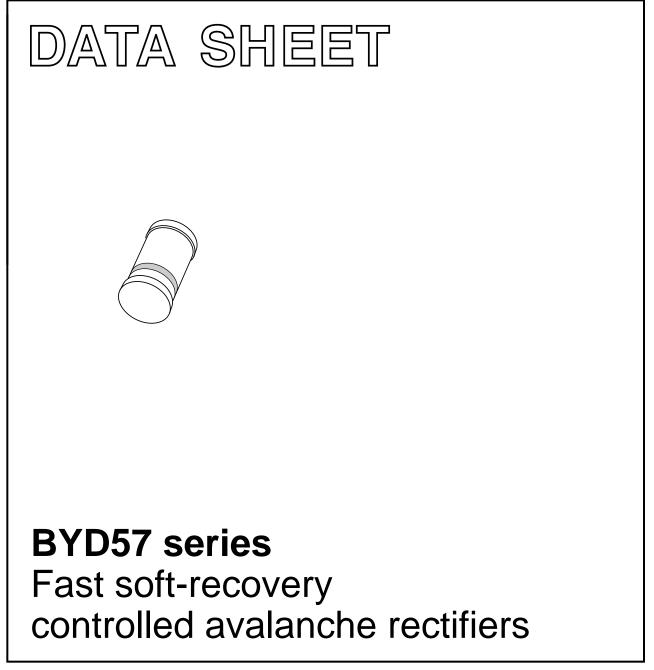
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of October 1993 File under Discrete Semiconductors, SC01 1996 Jun 05



High maximum operating temperature

FEATURES

- Low leakage current
- · Excellent stability

Glass passivated

- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier outline.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

V _{RRM}	repetitive peak reverse voltage				UNIT
	ropolitivo pour rovoroo voltago				
	BYD57D		_	200	V
	BYD57G		_	400	V
	BYD57J		_	600	V
	BYD57K		_	800	V
	BYD57M		_	1000	V
V _R	continuous reverse voltage				
	BYD57D		_	200	V
	BYD57G		_	400	V
	BYD57J		_	600	V
	BYD57K		_	800	V
	BYD57M		_	1000	V
I _{F(AV)}	average forward current	T _{tp} = 85 °C; see Fig.2; averaged over any 20 ms period; see also Fig.6	_	1.0	A
		T _{amb} = 60 °C; PCB mounting (see Fig.11); see Fig.3; averaged over any 20 ms period; see also Fig.6	_	0.4	A
I _{FRM}	repetitive peak forward current	T _{tp} = 85 °C; see Fig.4	_	8.5	A
		T _{amb} = 60 °C; see Fig.5	_	3.0	А
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sinewave; $T_j = 25 \text{ °C}$ prior to surge; $V_R = V_{RRMmax}$	_	5.0	A
E _{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j max}$ prior to surge; inductive load switched off	_	10	mJ
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature	see Fig.7	-65	+175	°C

DESCRIPTION

Cavity free cylindrical glass SOD87 package through Implotec^{TM(1)} technology. This package is

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hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

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Fig.1 Simplified outline (SOD87) and symbol.

MAM061

1996 Jun 05

BYD57 series

BYD57 series

ELECTRICAL CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 1 A; T_j = T_{j max};$ see Fig.8	_	_	2.1	V
		I _F = 1 A; see Fig.8	_	_	3.6	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA				
	BYD57D		300	_	_	V
	BYD57G		500	-	_	V
	BYD57J		700	_	-	V
	BYD57K		900	-	_	V
	BYD57M		1100	-	-	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig.9	_	_	5	μA
		$V_R = V_{RRMmax};$ T _j = 165 °C; see Fig.9	_	_	100	μA
t _{rr}	reverse recovery time BYD57D to J BYD57K and M	when switched from $I_F = 0.5 \text{ A to } I_R = 1 \text{ A}$; measured at $I_R = 0.25 \text{ A}$; see Fig.12	-	_	30 75	ns ns
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0 \text{ V};$ see Fig.10	-	20	_	pF
dl _R dt	maximum slope of reverse recovery current	when switched from $I_F = 1 A$ to $V_R \ge 30 V$				
1 1	BYD57D to J	and dI _F /dt = -1 A/µs; see Fig.13	-	-	7	A/μs
	BYD57K and M	300 I 19.13	—	_	6	A/μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		30	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.11. For more information please refer to the *'General Part of Handbook SC01'*.

BYD57 series

Product specification

GRAPHICAL DATA

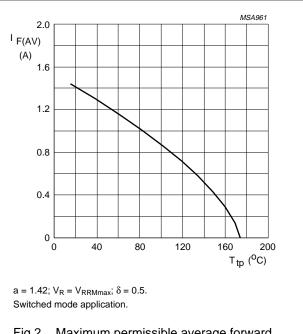


Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

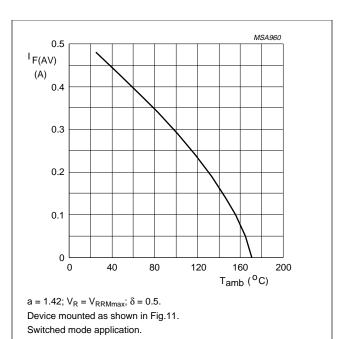


Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

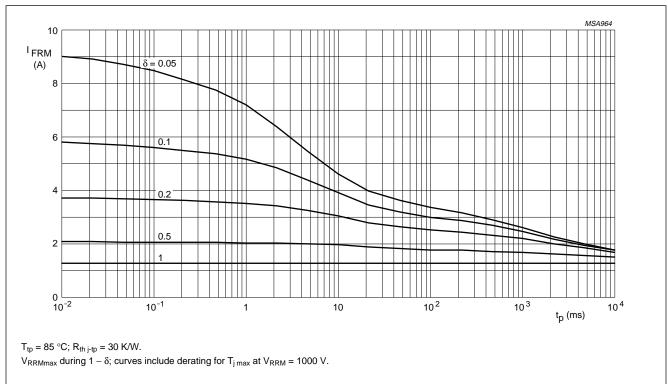
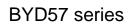
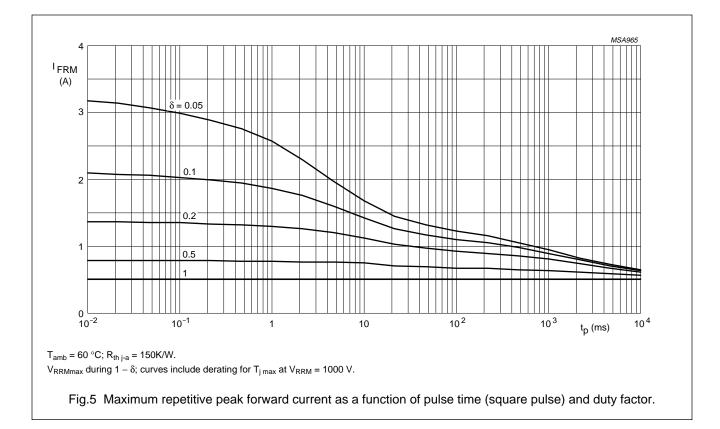
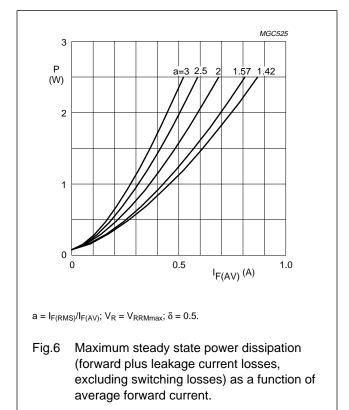


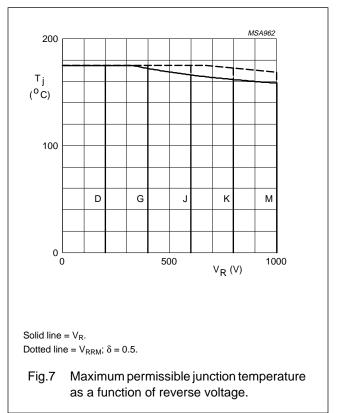
Fig.4 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

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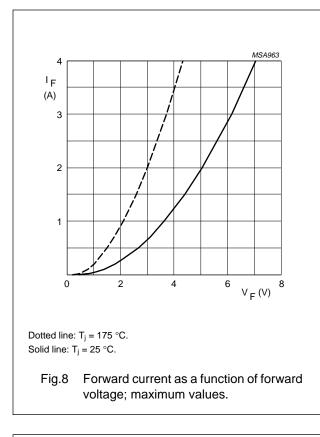


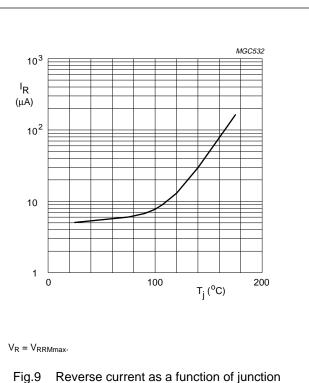


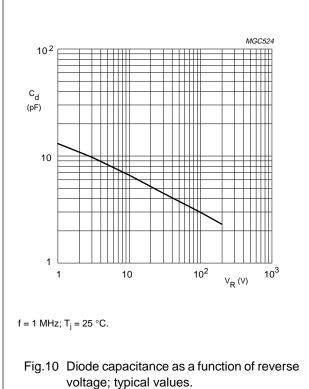


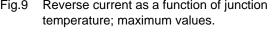


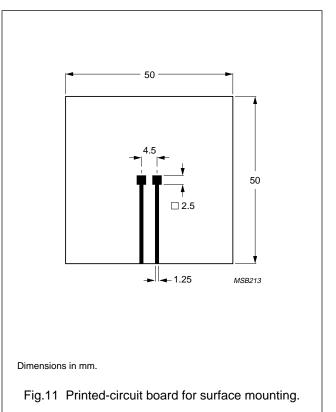
BYD57 series



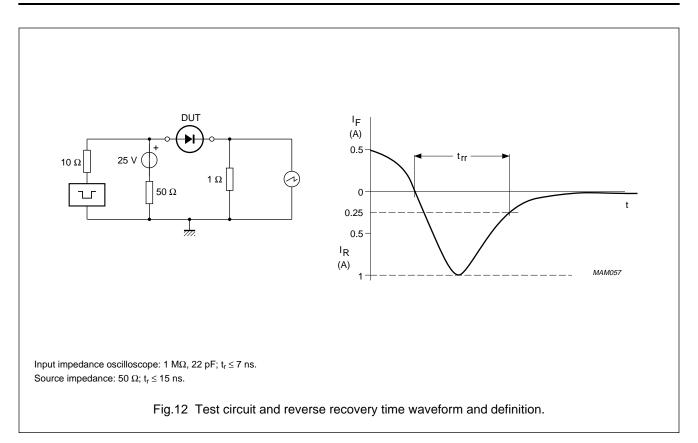


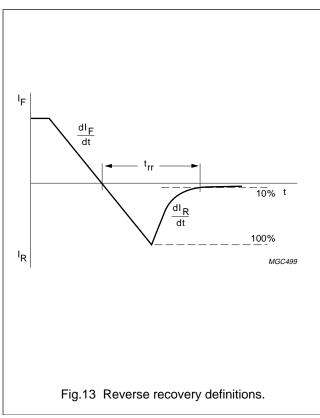






BYD57 series

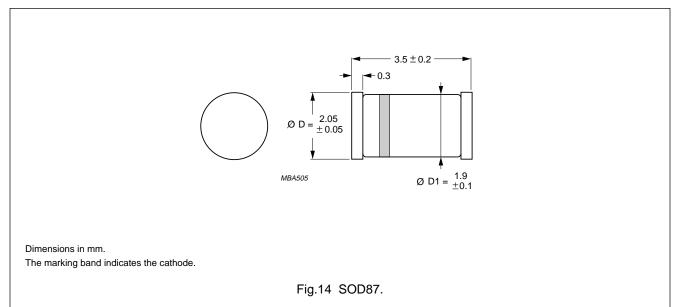




Product specification

BYD57 series

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
more of the limiting values i of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.
Application information	
Where application informati	on is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.